

IGBT

High speed IGBT in Trench and Fieldstop technology
recommended in combination with SiC Diode IDH15S120

IGW25N120H3

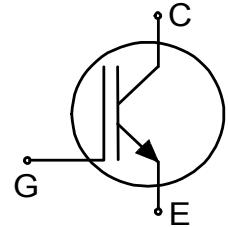
1200V high speed switching series third generation

Data sheet

High speed IGBT in Trench and Fieldstop technology recommended in combination with SiC Diode IDH15S120

Features:

- TRENCHSTOP™ technology offering
- best in class switching performance: less than 500µJ total switching losses achievable
 - very low V_{CEsat}
 - low EMI
 - maximum junction temperature 175°C
 - qualified according to JEDEC for target applications
 - Pb-free lead plating; RoHS compliant
 - complete product spectrum and PSpice Models: <http://www.infineon.com/igbt/>



Applications:

- solar inverters
- uninterruptible power supplies
- welding converters
- converters with high switching frequency



Package pin definition:

- Pin 1 - gate
- Pin 2 & backside - collector
- Pin 3 - emitter



Key Performance and Package Parameters

| Type | V_{CE} | I_C | $V_{CEsat}, T_{vj}=25^{\circ}C$ | T_{vjmax} | Marking | Package |
|-------------|----------|-------|---------------------------------|-------------|----------|------------|
| IGW25N120H3 | 1200V | 25A | 2.05V | 175°C | G25H1203 | PG-TO247-3 |



Table of Contents

Description 2

Table of Contents 3

Maximum ratings 4

Thermal Resistance 4

Electrical Characteristics 4

Electrical Characteristics diagrams 7

Package Drawing13

Testing Conditions14

Revision History15

Disclaimer15

Maximum ratings

| Parameter | Symbol | Value | Unit |
|---|-------------|----------------|------------------|
| Collector-emitter voltage | V_{CE} | 1200 | V |
| DC collector current, limited by T_{vjmax} $T_C = 25^\circ\text{C}$ $T_C = 100^\circ\text{C}$ | I_C | 50.0 25.0 | A |
| Pulsed collector current, t_p limited by T_{vjmax} | I_{Cpuls} | 100.0 | A |
| Turn off safe operating area $V_{CE} \leq 1200\text{V}$, $T_{vj} \leq 175^\circ\text{C}$ | - | 100.0 | A |
| Gate-emitter voltage | V_{GE} | ± 20 | V |
| Short circuit withstand time $V_{GE} = 15.0\text{V}$, $V_{CC} \leq 600\text{V}$ Allowed number of short circuits < 1000 Time between short circuits: $\geq 1.0\text{s}$ $T_{vj} = 175^\circ\text{C}$ | t_{SC} | 10 | μs |
| Power dissipation $T_C = 25^\circ\text{C}$ Power dissipation $T_C = 100^\circ\text{C}$ | P_{tot} | 326.0 156.0 | W |
| Operating junction temperature | T_{vj} | -40...+175 | $^\circ\text{C}$ |
| Storage temperature | T_{stg} | -55...+150 | $^\circ\text{C}$ |
| Soldering temperature, wave soldering 1.6 mm (0.063 in.) from case for 10s | | 260 | $^\circ\text{C}$ |
| Mounting torque, M3 screw Maximum of mounting processes: 3 | M | 0.6 | Nm |

Thermal Resistance

| Parameter | Symbol | Conditions | Max. Value | Unit |
|---|---------------|------------|------------|------|
| Characteristic | | | | |
| IGBT thermal resistance, junction - case | $R_{th(j-c)}$ | | 0.46 | K/W |
| Thermal resistance junction - ambient | $R_{th(j-a)}$ | | 40 | K/W |

Electrical Characteristic, at $T_{vj} = 25^\circ\text{C}$, unless otherwise specified

| Parameter | Symbol | Conditions | Value | | | Unit |
|--------------------------------------|---------------|---|-------------|----------------------|-----------------|---------------|
| | | | min. | typ. | max. | |
| Static Characteristic | | | | | | |
| Collector-emitter breakdown voltage | $V_{(BR)CES}$ | $V_{GE} = 0\text{V}$, $I_C = 0.50\text{mA}$ | 1200 | - | - | V |
| Collector-emitter saturation voltage | V_{CEsat} | $V_{GE} = 15.0\text{V}$, $I_C = 25.0\text{A}$ $T_{vj} = 25^\circ\text{C}$ $T_{vj} = 125^\circ\text{C}$ $T_{vj} = 175^\circ\text{C}$ | - - - | 2.05 2.50 2.70 | 2.40 - - | V |
| Gate-emitter threshold voltage | $V_{GE(th)}$ | $I_C = 0.85\text{mA}$, $V_{CE} = V_{GE}$ | 5.0 | 5.8 | 6.5 | V |
| Zero gate voltage collector current | I_{CES} | $V_{CE} = 1200\text{V}$, $V_{GE} = 0\text{V}$ $T_{vj} = 25^\circ\text{C}$ $T_{vj} = 175^\circ\text{C}$ | - - | - - | 250.0 2500.0 | μA |
| Gate-emitter leakage current | I_{GES} | $V_{CE} = 0\text{V}$, $V_{GE} = 20\text{V}$ | - | - | 600 | nA |
| Transconductance | g_{fs} | $V_{CE} = 20\text{V}$, $I_C = 25.0\text{A}$ | - | 13.0 | - | S |

Electrical Characteristic, at $T_{vj} = 25^{\circ}\text{C}$, unless otherwise specified

| Parameter | Symbol | Conditions | Value | | | Unit |
|--|-------------|---|-------|-------|------|------|
| | | | min. | typ. | max. | |
| Dynamic Characteristic | | | | | | |
| Input capacitance | C_{ies} | $V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$ | - | 1430 | - | pF |
| Output capacitance | C_{oes} | | - | 95 | - | |
| Reverse transfer capacitance | C_{res} | | - | 75 | - | |
| Gate charge | Q_G | $V_{CC} = 960\text{V}, I_C = 25.0\text{A}, V_{GE} = 15\text{V}$ | - | 115.0 | - | nC |
| Short circuit collector current Max. 1000 short circuits Time between short circuits: $\geq 1.0\text{s}$ | $I_{C(SC)}$ | $V_{GE} = 15.0\text{V}, V_{CC} \leq 600\text{V}, t_{SC} \leq 10\mu\text{s}, T_{vj} = 175^{\circ}\text{C}$ | - | 87 | - | A |

Switching Characteristic, Inductive Load

| Parameter | Symbol | Conditions | Value | | | Unit |
|---|--------------|--|-------|------|------|------|
| | | | min. | typ. | max. | |
| IGBT Characteristic, at $T_{vj} = 25^{\circ}\text{C}$ | | | | | | |
| Turn-on delay time | $t_{d(on)}$ | $T_{vj} = 25^{\circ}\text{C}, V_{CC} = 600\text{V}, I_C = 25.0\text{A}, V_{GE} = 0.0/15.0\text{V}, r_G = 23.0\Omega, L\sigma = 80\text{nH}, C\sigma = 67\text{pF}$ $L\sigma, C\sigma$ from Fig. E Energy losses include "tail" and diode (IKW25N120H3) reverse recovery. | - | 27 | - | ns |
| Rise time | t_r | | - | 41 | - | ns |
| Turn-off delay time | $t_{d(off)}$ | | - | 277 | - | ns |
| Fall time | t_f | | - | 17 | - | ns |
| Turn-on energy | E_{on} | | - | 1.80 | - | mJ |
| Turn-off energy | E_{off} | | - | 0.85 | - | mJ |
| Total switching energy | E_{ts} | | - | 2.65 | - | mJ |
| Turn-on energy | E_{on} | $T_{vj} = 25^{\circ}\text{C}, V_{CC} = 800\text{V}, I_C = 10.0\text{A}, V_{GE} = 0.0/15.0\text{V}, r_G = 3.0\Omega, L\sigma = 80\text{nH}, C\sigma = 67\text{pF}$ $L\sigma, C\sigma$ from Fig. E Energy losses include "tail" and diode (IDH15S120) reverse recovery. | - | 0.08 | - | mJ |
| Turn-off energy | E_{off} | | - | 0.27 | - | mJ |
| Total switching energy | E_{ts} | | - | 0.35 | - | mJ |

Switching Characteristic, Inductive Load

| Parameter | Symbol | Conditions | Value | | | Unit |
|--|--------------|--|-------|------|------|------|
| | | | min. | typ. | max. | |
| IGBT Characteristic, at $T_{vj} = 175^{\circ}\text{C}$ | | | | | | |
| Turn-on delay time | $t_{d(on)}$ | $T_{vj} = 175^{\circ}\text{C}$, $V_{CC} = 600\text{V}$, $I_C = 25.0\text{A}$, $V_{GE} = 0.0/15.0\text{V}$, $r_G = 23.0\Omega$, $L\sigma = 80\text{nH}$, $C\sigma = 67\text{pF}$ $L\sigma$, $C\sigma$ from Fig. E Energy losses include "tail" and diode (IKW25N120H3) reverse recovery. | - | 26 | - | ns |
| Rise time | t_r | | - | 35 | - | ns |
| Turn-off delay time | $t_{d(off)}$ | | - | 347 | - | ns |
| Fall time | t_f | | - | 50 | - | ns |
| Turn-on energy | E_{on} | | - | 2.60 | - | mJ |
| Turn-off energy | E_{off} | | - | 1.70 | - | mJ |
| Total switching energy | E_{ts} | | - | 4.30 | - | mJ |
| Turn-on energy | E_{on} | $T_{vj} = 175^{\circ}\text{C}$, $V_{CC} = 800\text{V}$, $I_C = 10.0\text{A}$, $V_{GE} = 0.0/15.0\text{V}$, $r_G = 3.0\Omega$, $L\sigma = 80\text{nH}$, $C\sigma = 67\text{pF}$ $L\sigma$, $C\sigma$ from Fig. E Energy losses include "tail" and diode (IDH15S120) reverse recovery. | - | 0.10 | - | mJ |
| Turn-off energy | E_{off} | | - | 0.62 | - | mJ |
| Total switching energy | E_{ts} | | - | 0.72 | - | mJ |

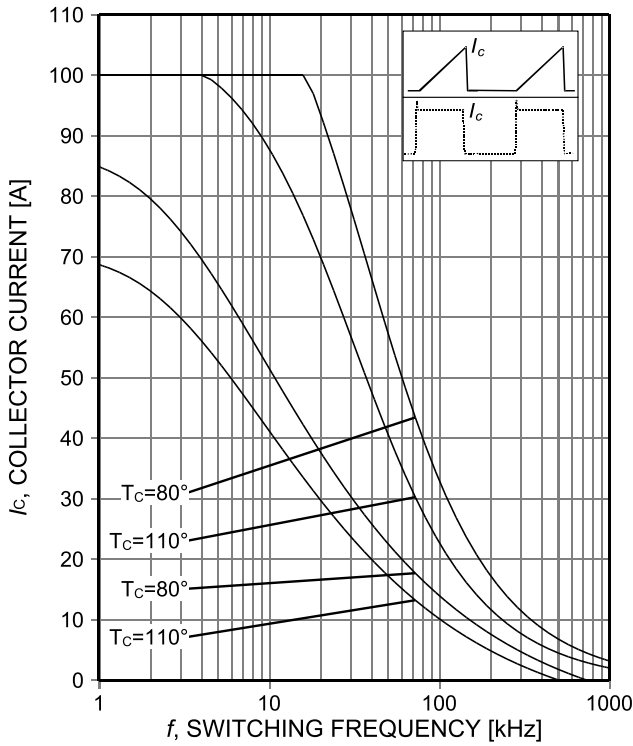


Figure 1. **Collector current as a function of switching frequency**
 ($T_j \leq 175^\circ\text{C}$, $D=0.5$, $V_{CE}=600\text{V}$, $V_{GE}=15/0\text{V}$, $r_G=23\Omega$)

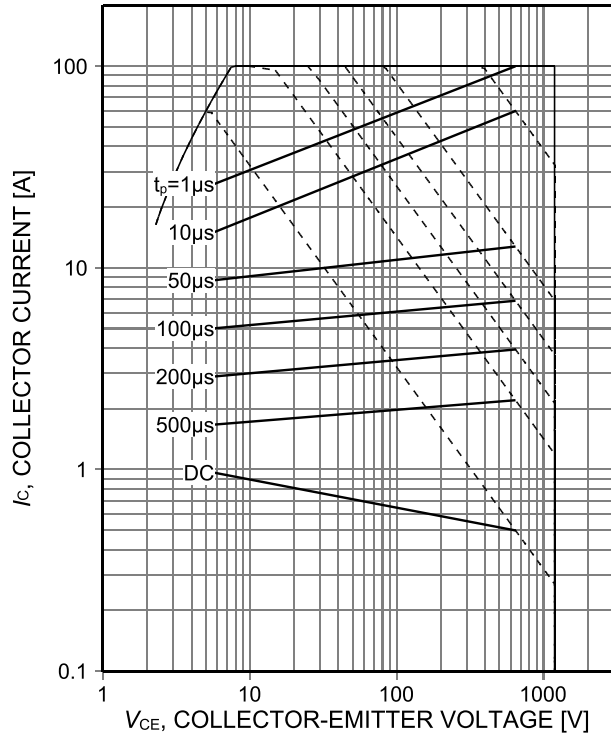


Figure 2. **Forward bias safe operating area**
 ($D=0$, $T_C=25^\circ\text{C}$, $T_j \leq 175^\circ\text{C}$; $V_{GE}=15\text{V}$)

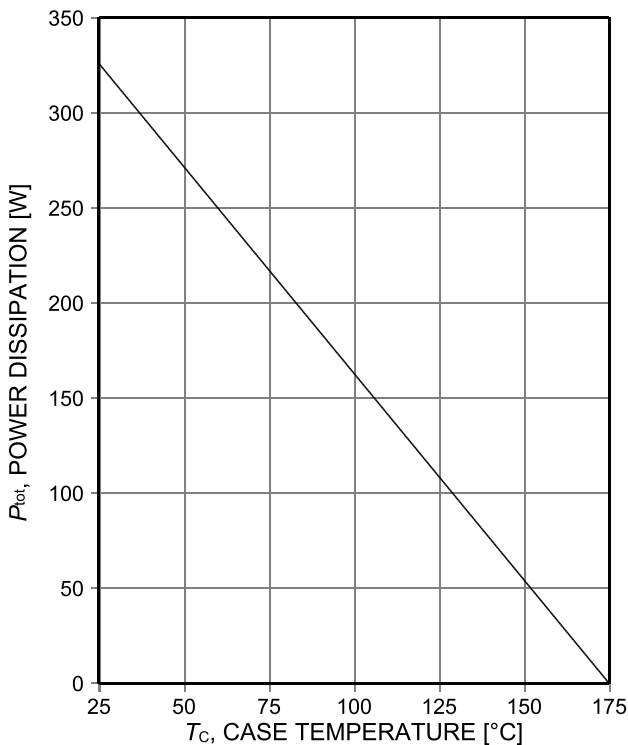


Figure 3. **Power dissipation as a function of case temperature**
 ($T_j \leq 175^\circ\text{C}$)

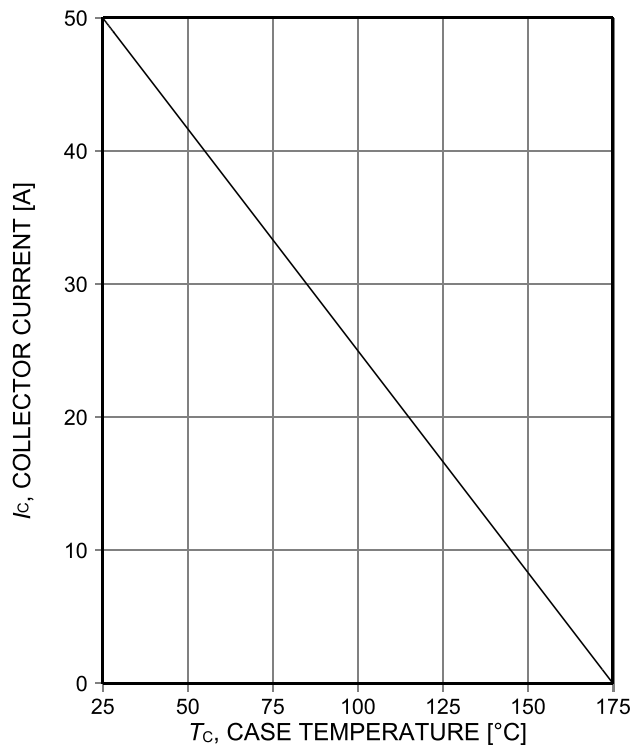


Figure 4. **Collector current as a function of case temperature**
 ($V_{GE} \geq 15\text{V}$, $T_j \leq 175^\circ\text{C}$)

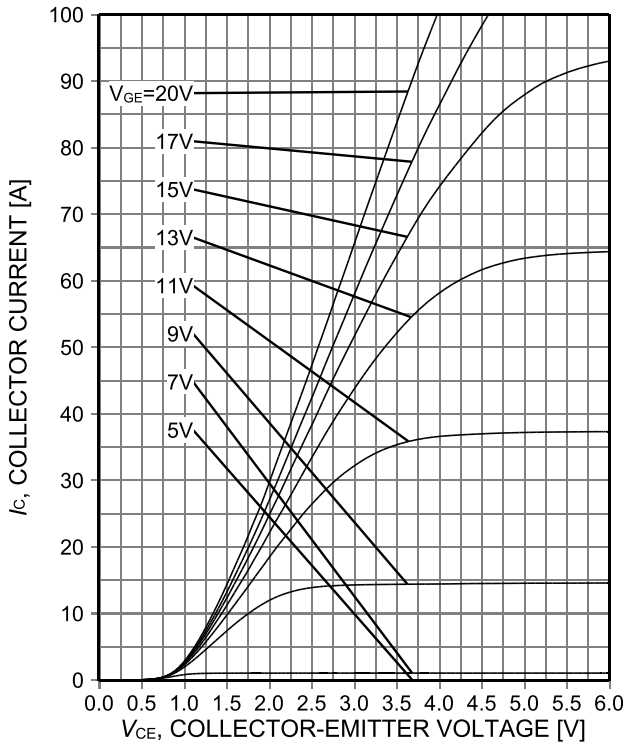


Figure 5. **Typical output characteristic**
($T_j=25^\circ\text{C}$)

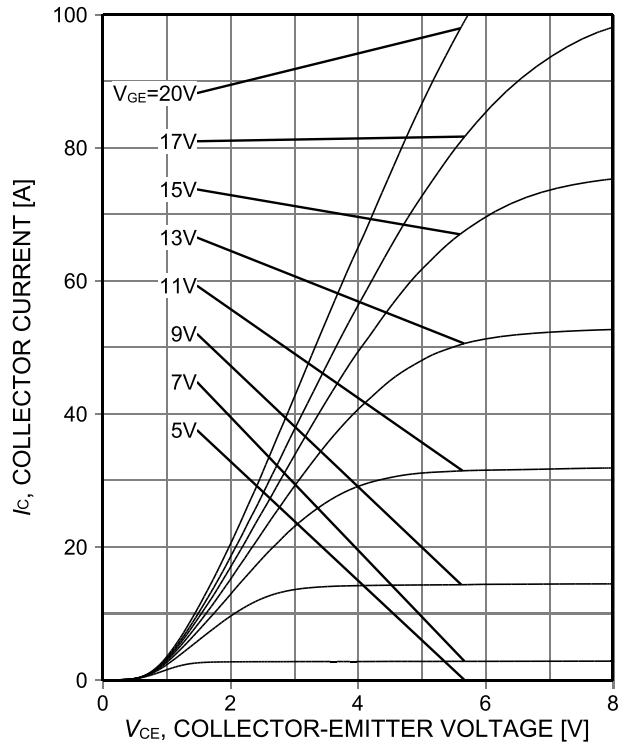


Figure 6. **Typical output characteristic**
($T_j=175^\circ\text{C}$)

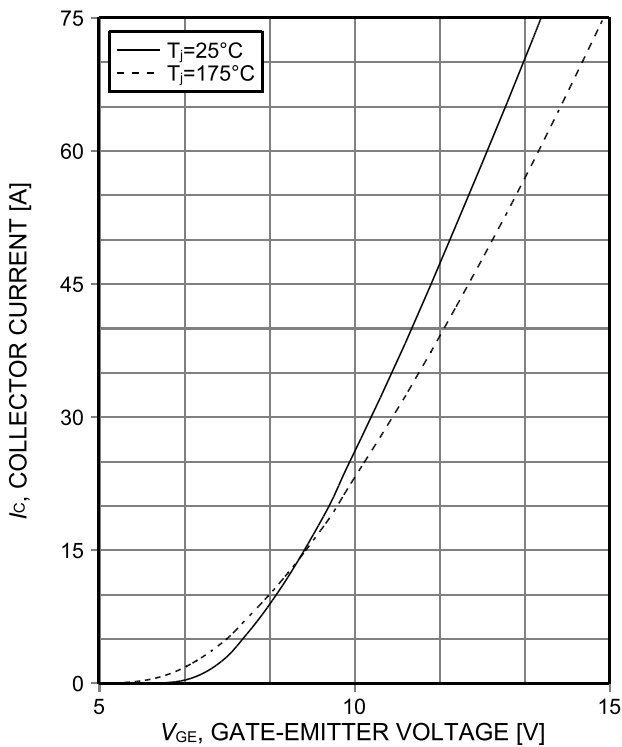


Figure 7. **Typical transfer characteristic**
($V_{CE}=20\text{V}$)

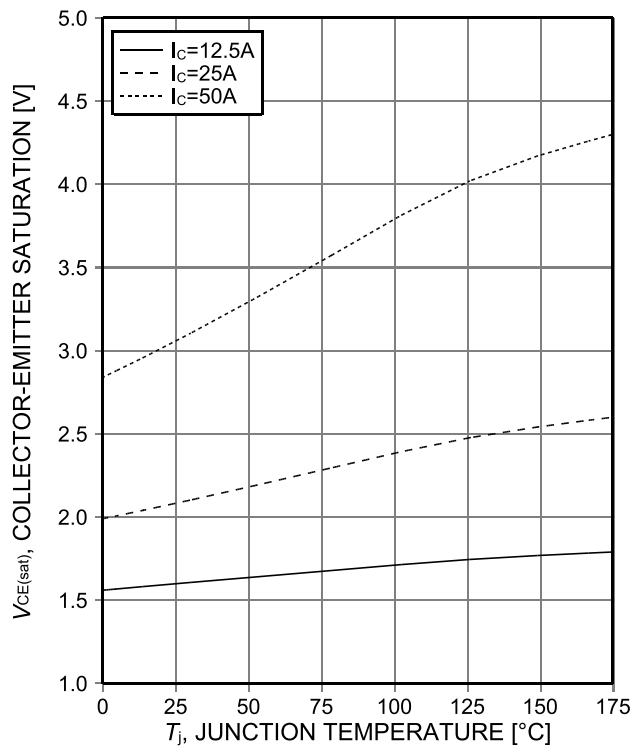


Figure 8. **Typical collector-emitter saturation voltage as a function of junction temperature**
($V_{GE}=15\text{V}$)

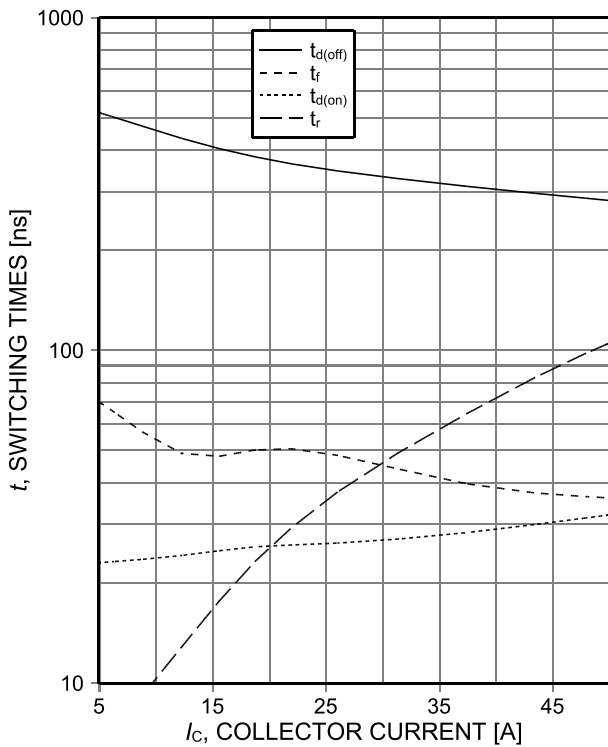


Figure 9. **Typical switching times as a function of collector current**
 (ind. load, $T_j=175^\circ\text{C}$, $V_{CE}=600\text{V}$, $V_{GE}=15/0\text{V}$, $r_G=23\Omega$, test circuit in Fig. E)

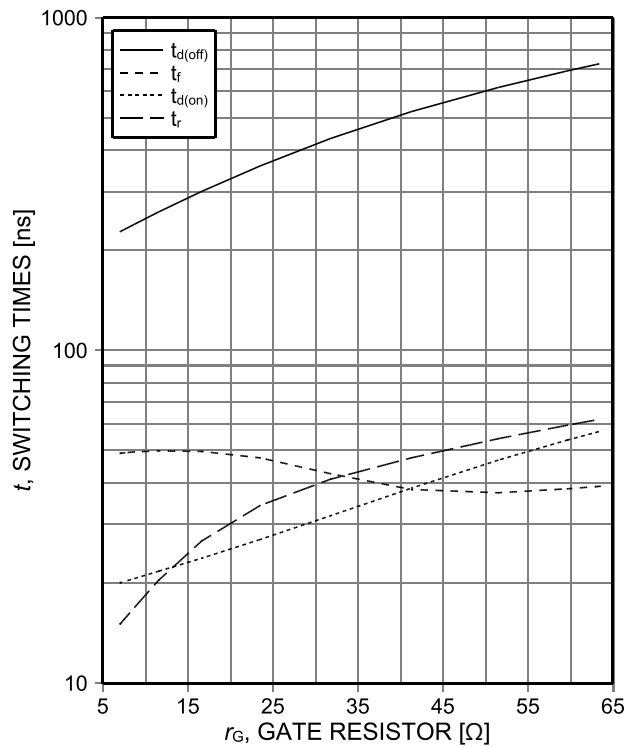


Figure 10. **Typical switching times as a function of gate resistor**
 (ind. load, $T_j=175^\circ\text{C}$, $V_{CE}=600\text{V}$, $V_{GE}=15/0\text{V}$, $I_C=25\text{A}$, test circuit in Fig. E)

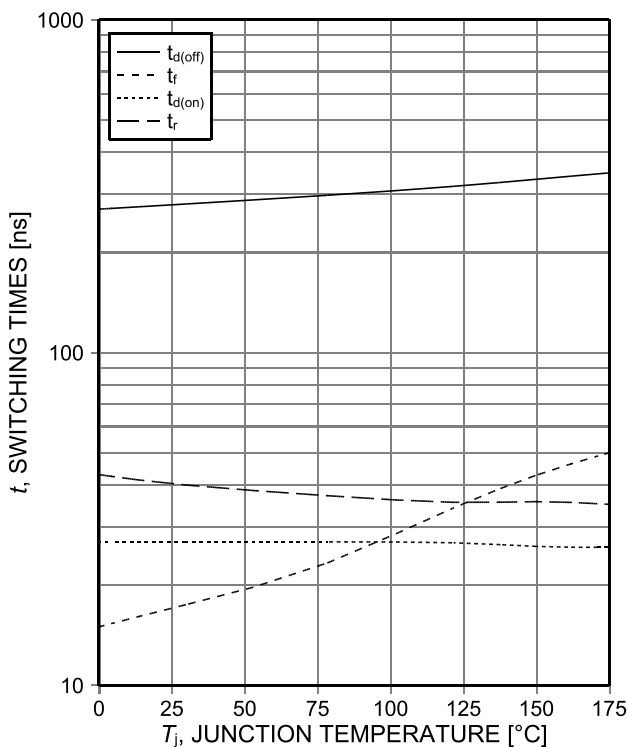


Figure 11. **Typical switching times as a function of junction temperature**
 (ind. load, $V_{CE}=600\text{V}$, $V_{GE}=15/0\text{V}$, $I_C=25\text{A}$, $r_G=23\Omega$, test circuit in Fig. E)

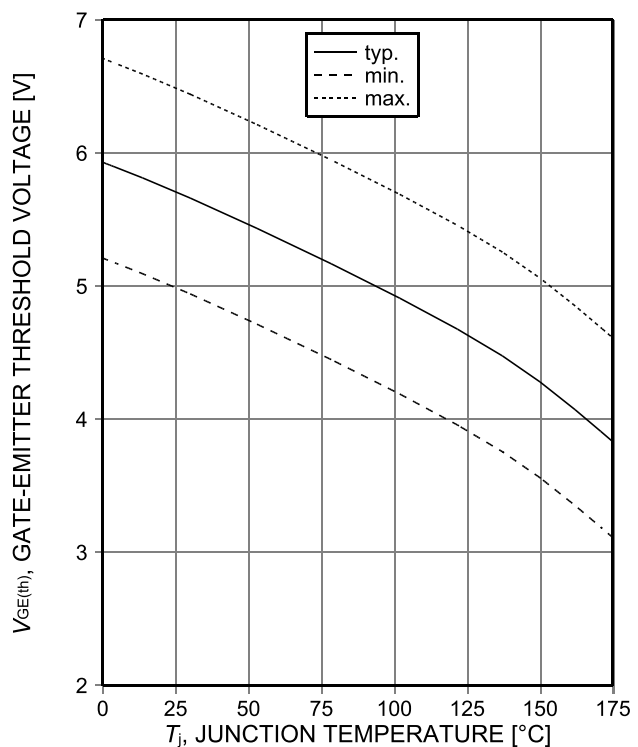


Figure 12. **Gate-emitter threshold voltage as a function of junction temperature**
 ($I_C=0.85\text{mA}$)

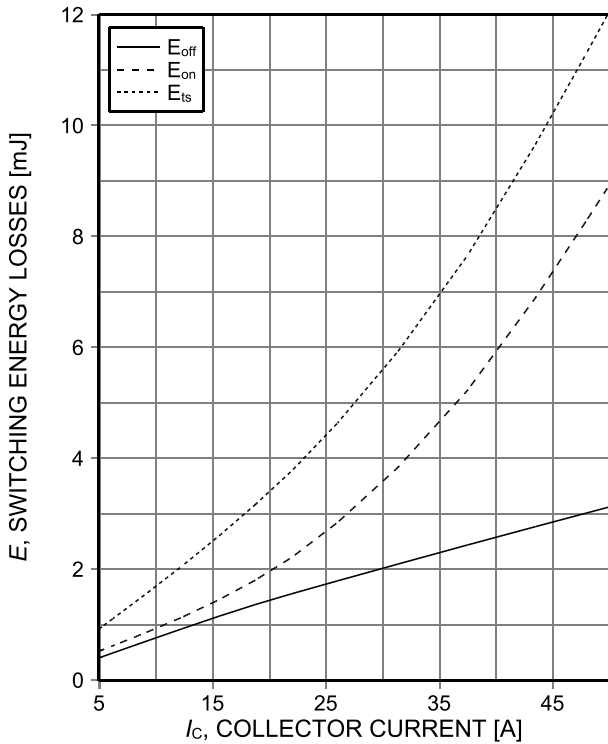


Figure 13. **Typical switching energy losses as a function of collector current**
 (ind. load, $T_j=175^\circ\text{C}$, $V_{CE}=600\text{V}$, $V_{GE}=15/0\text{V}$, $r_G=23\Omega$, test circuit in Fig. E)

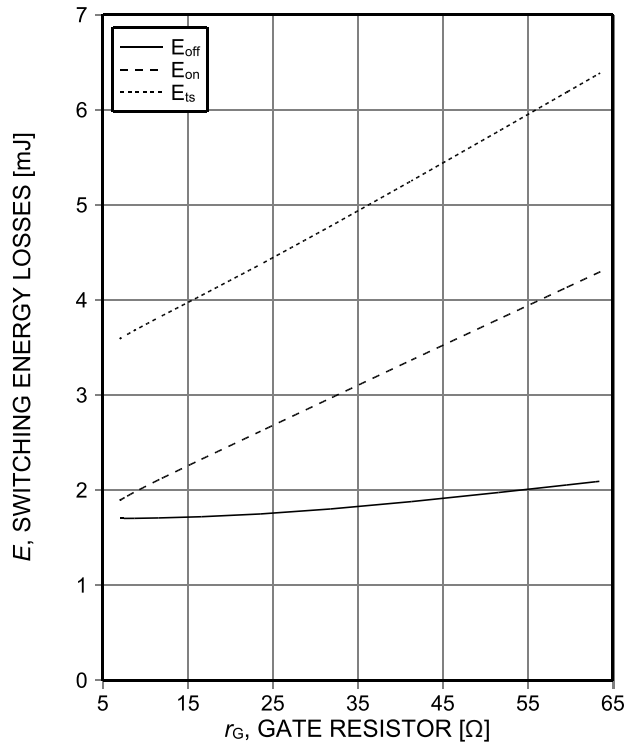


Figure 14. **Typical switching energy losses as a function of gate resistor**
 (ind. load, $T_j=175^\circ\text{C}$, $V_{CE}=600\text{V}$, $V_{GE}=15/0\text{V}$, $I_c=25\text{A}$, test circuit in Fig. E)

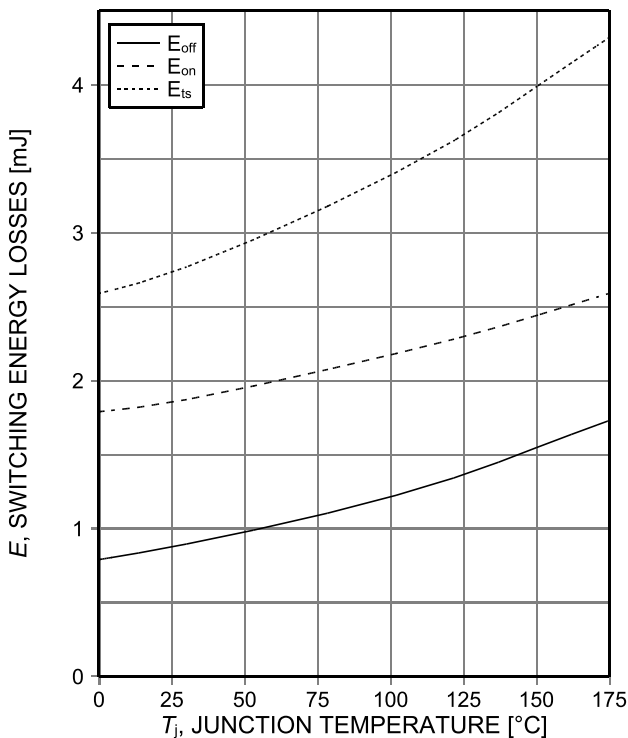


Figure 15. **Typical switching energy losses as a function of junction temperature**
 (ind load, $V_{CE}=600\text{V}$, $V_{GE}=15/0\text{V}$, $I_c=25\text{A}$, $r_G=23\Omega$, test circuit in Fig. E)

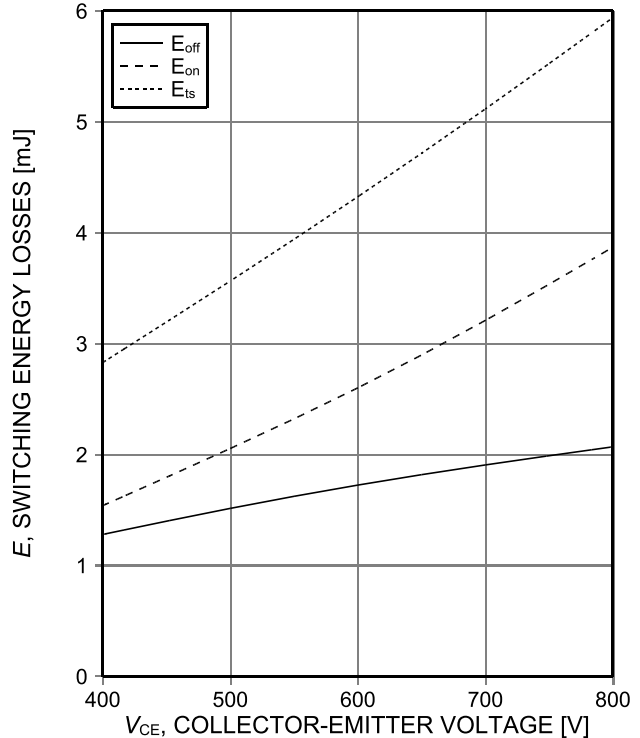


Figure 16. **Typical switching energy losses as a function of collector emitter voltage**
 (ind. load, $T_j=175^\circ\text{C}$, $V_{GE}=15/0\text{V}$, $I_c=25\text{A}$, $r_G=23\Omega$, test circuit in Fig. E)

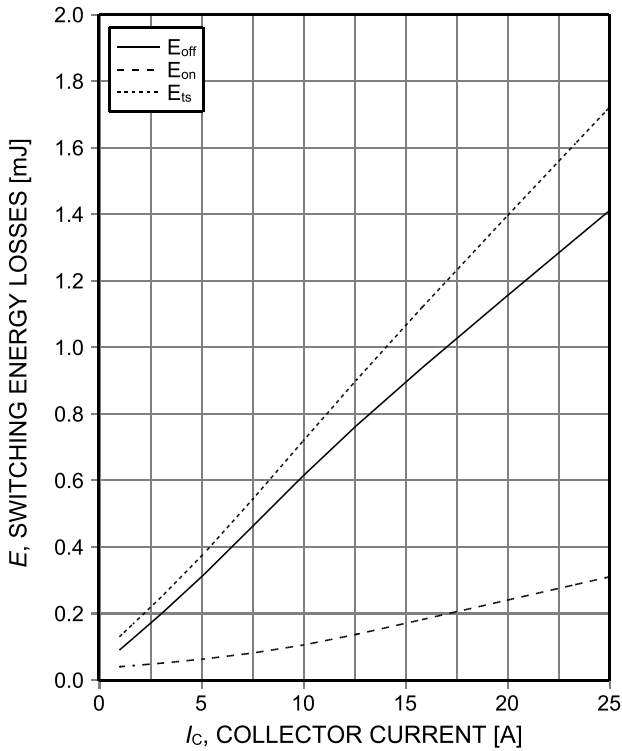


Figure 1. Typical switching energy losses as a function of collector current (ind. load, $T_j=125^\circ\text{C}$, $V_{CE}=800\text{V}$, $V_{GE}=15/0\text{V}$, $r_G=3\Omega$, Diode IDH15S120)

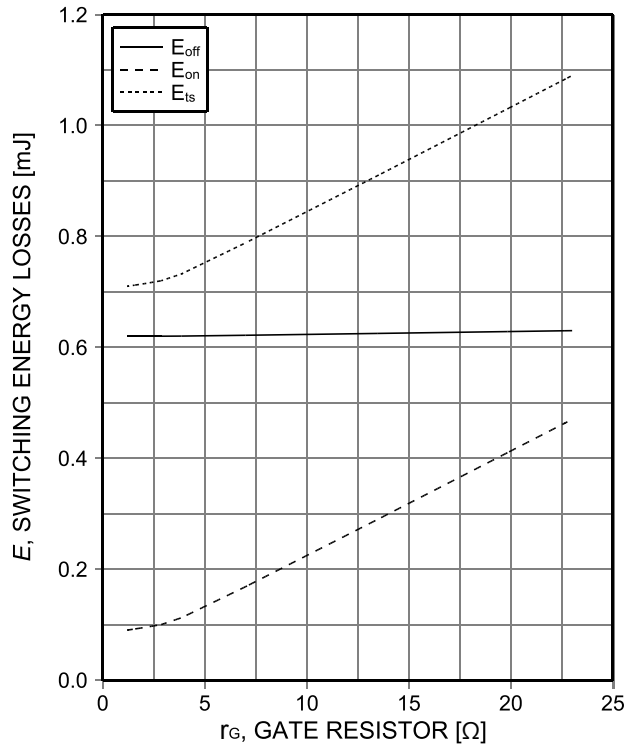


Figure 2. Typical switching energy losses as a function of gate resistor (ind. load, $T_j=125^\circ\text{C}$, $V_{CE}=800\text{V}$, $V_{GE}=15/0\text{V}$, $I_C=10\text{A}$, Diode IDH15S120)

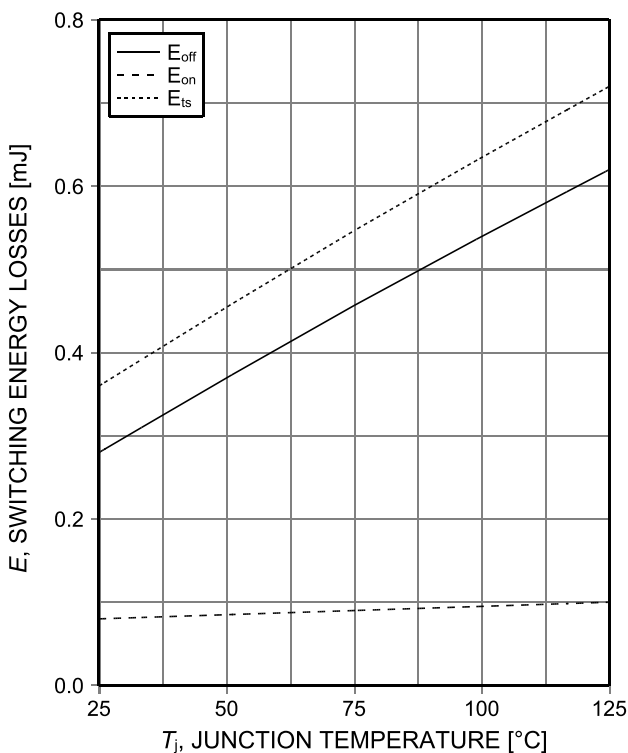


Figure 3. Typical switching energy losses as a function of junction temperature (ind. load, $V_{CE}=800\text{V}$, $V_{GE}=15/0\text{V}$, $I_C=10\text{A}$, $r_G=3\Omega$, Diode IDH15S120)

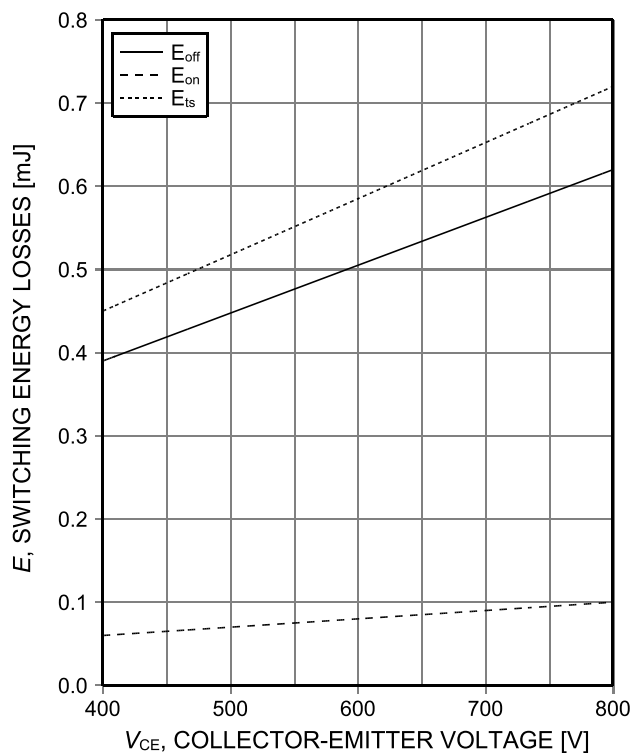


Figure 4. Typical switching energy losses as a function of collector emitter voltage (ind. load, $T_j=125^\circ\text{C}$, $V_{GE}=15/0\text{V}$, $I_C=10\text{A}$, $r_G=3\Omega$, Diode IDH15S120)

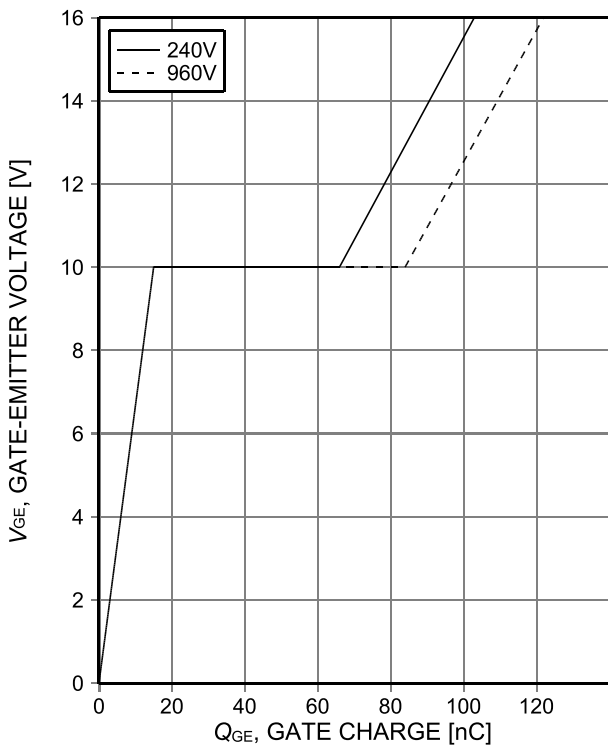


Figure 17. **Typical gate charge**
($I_C=25A$)

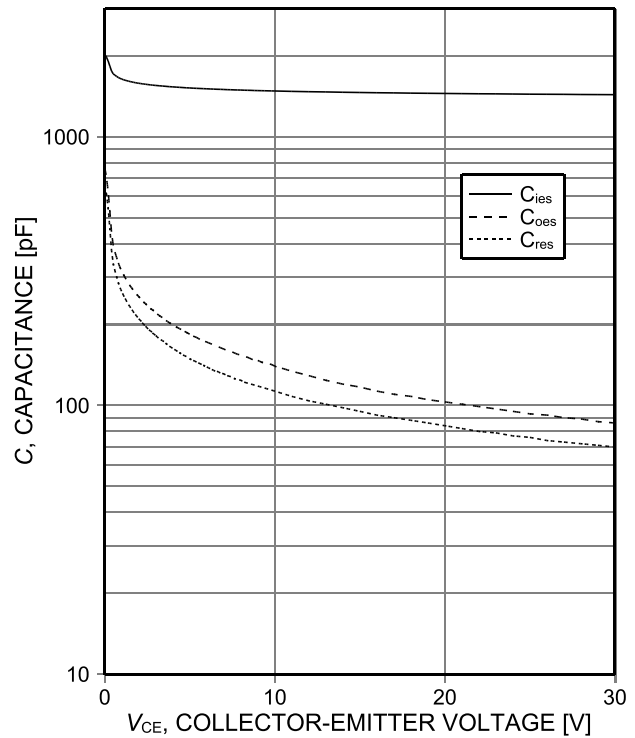


Figure 18. **Typical capacitance as a function of collector-emitter voltage**
($V_{GE}=0V$, $f=1MHz$)

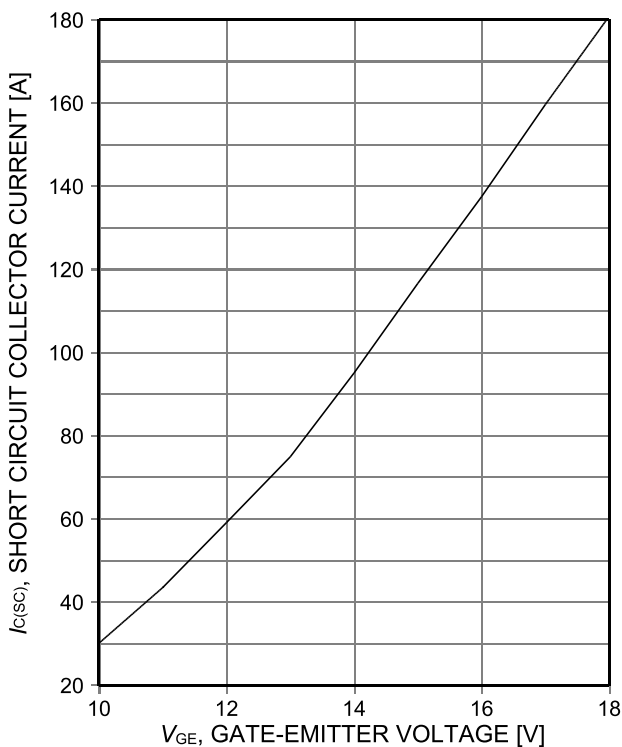


Figure 19. **Typical short circuit collector current as a function of gate-emitter voltage**
($V_{CE}\leq 600V$, start at $T_j=25^\circ C$)

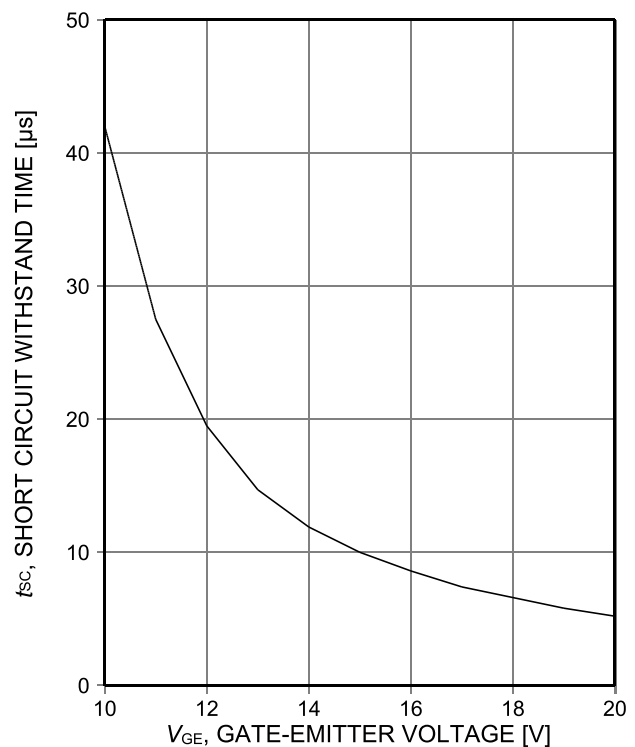


Figure 20. **Short circuit withstand time as a function of gate-emitter voltage**
($V_{CE}\leq 600V$, start at $T_j\leq 150^\circ C$)

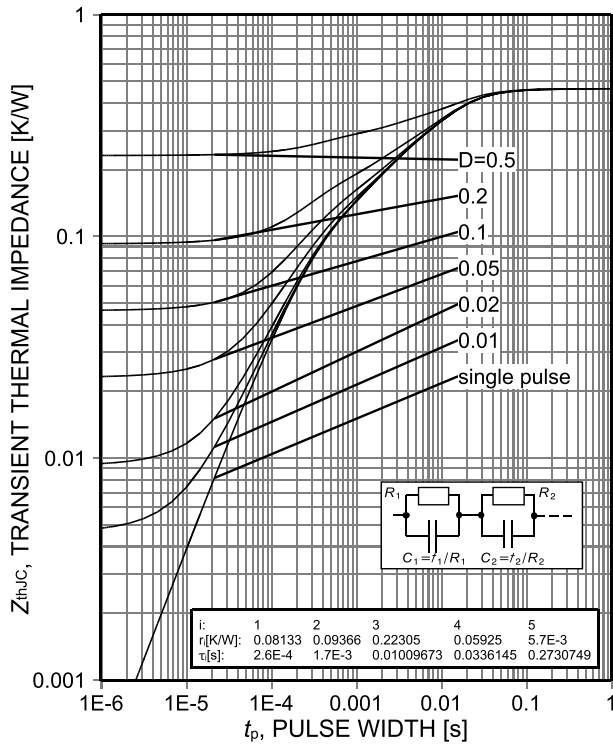
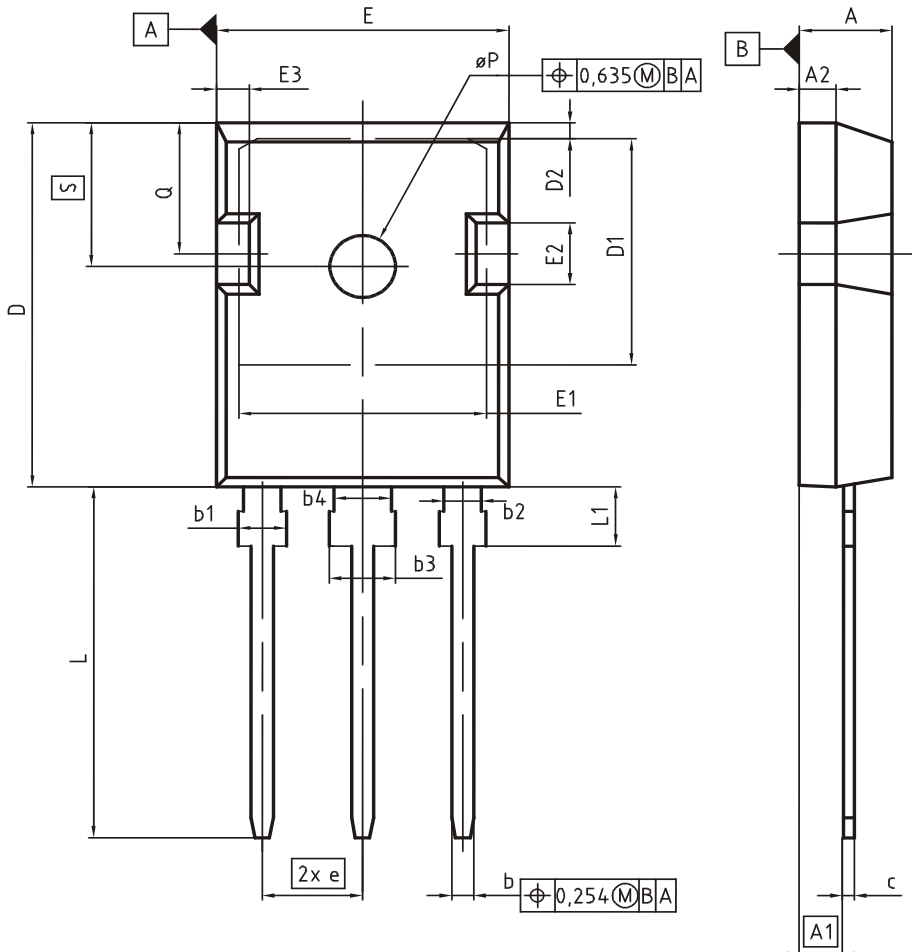


Figure 21. IGBT transient thermal impedance ($D=t_p/T$)

PG-TO247-3



| DIM | MILLIMETERS | | INCHES | |
|-----|-------------|-------|-------------|-------|
| | MIN | MAX | MIN | MAX |
| A | 4.83 | 5.21 | 0.190 | 0.205 |
| A1 | 2.27 | 2.54 | 0.089 | 0.100 |
| A2 | 1.85 | 2.16 | 0.073 | 0.085 |
| b | 1.07 | 1.33 | 0.042 | 0.052 |
| b1 | 1.90 | 2.41 | 0.075 | 0.095 |
| b2 | 1.90 | 2.16 | 0.075 | 0.085 |
| b3 | 2.87 | 3.38 | 0.113 | 0.133 |
| b4 | 2.87 | 3.13 | 0.113 | 0.123 |
| c | 0.55 | 0.68 | 0.022 | 0.027 |
| D | 20.80 | 21.10 | 0.819 | 0.831 |
| D1 | 16.25 | 17.65 | 0.640 | 0.695 |
| D2 | 0.95 | 1.35 | 0.037 | 0.053 |
| E | 15.70 | 16.13 | 0.618 | 0.635 |
| E1 | 13.10 | 14.15 | 0.516 | 0.557 |
| E2 | 3.68 | 5.10 | 0.145 | 0.201 |
| E3 | 1.00 | 2.60 | 0.039 | 0.102 |
| e | 5.44 (BSC) | | 0.214 (BSC) | |
| N | 3 | | 3 | |
| L | 19.80 | 20.32 | 0.780 | 0.800 |
| L1 | 4.10 | 4.47 | 0.161 | 0.176 |
| øP | 3.50 | 3.70 | 0.138 | 0.146 |
| Q | 5.49 | 6.00 | 0.216 | 0.236 |
| S | 6.04 | 6.30 | 0.238 | 0.248 |

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SCALE

EUROPEAN PROJECTION

ISSUE DATE
09-07-2010

REVISION
05

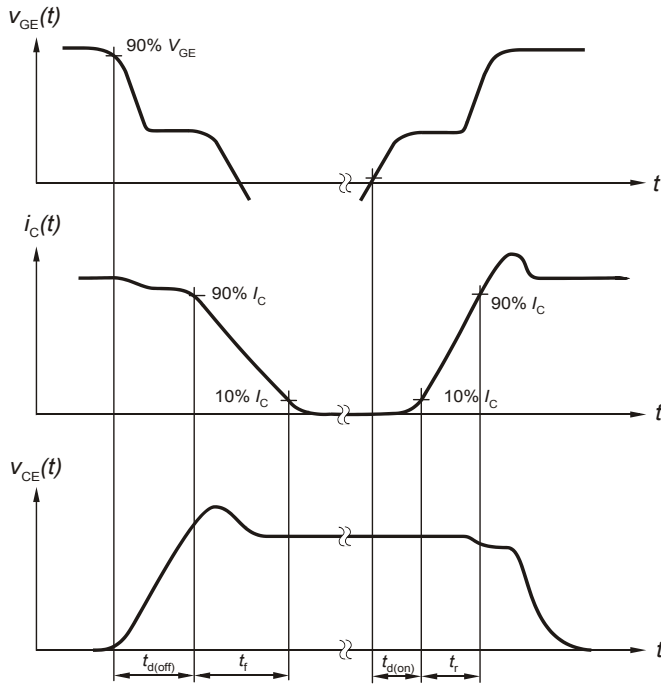


Figure A. Definition of switching times

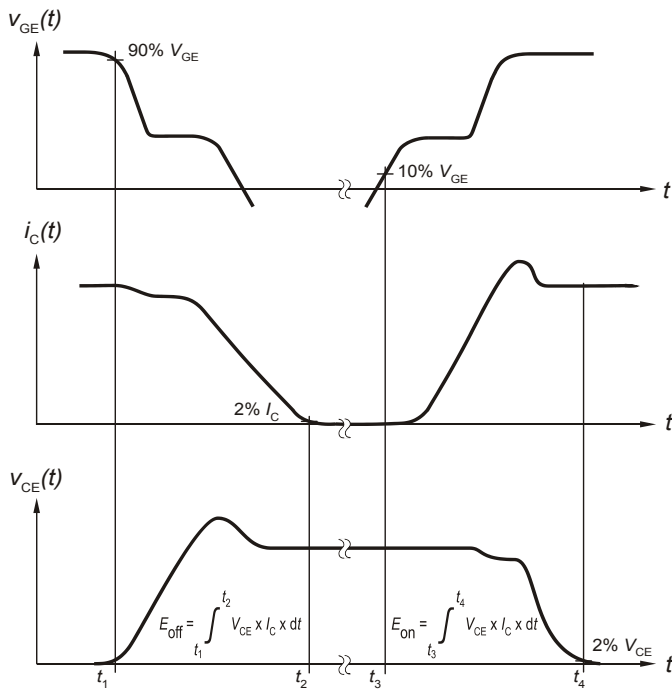


Figure B. Definition of switching losses

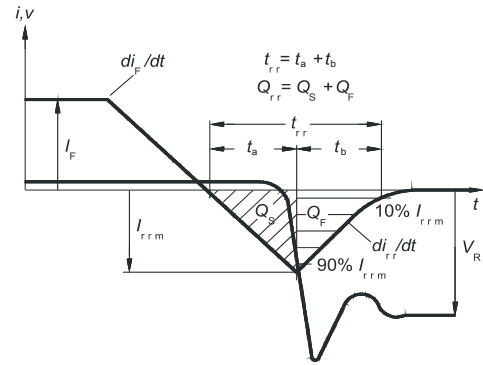


Figure C. Definition of diodes switching characteristics

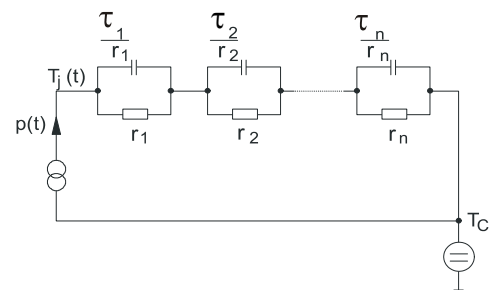


Figure D. Thermal equivalent circuit

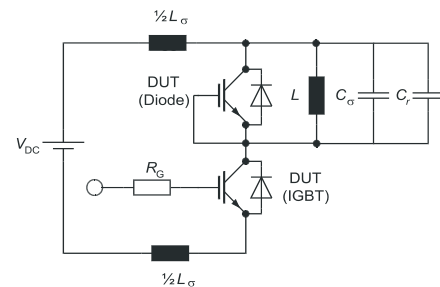


Figure E. Dynamic test circuit
Parasitic inductance L_σ ,
Parasitic capacitor C_σ ,
Relief capacitor C_r
(only for ZVT switching)

Revision History

IGW25N120H3

Revision: 2014-02-27, Rev. 2.1

Previous Revision

| Revision | Date | Subjects (major changes since last revision) |
|----------|------------|--|
| 1.1 | 2011-12-12 | Preliminary data sheet |
| 2.1 | 2014-02-27 | Final data sheet |

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